



PATENT
Customer No. 22,852
Attorney Docket No. 07553.0017

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
Mitsuru ISHIKAWA et al.)
Application No.: 09/696,232 ✓) Group Art Unit: 1763
Filed: October 26, 2000) Examiner: A. Olsen
For: ETCHING METHOD)

Commissioner for Patents
Washington, DC 20231

Sir:

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AMENDMENT

In reply to the Office Action dated December 19, 2002, please amend the application as follows:

IN THE SPECIFICATION:

Page 2, please amend the paragraph beginning with "In order to" to read as follows:

(Amended) In order to achieve the object described above, in a first aspect of the present invention, an etching method for etching an etching target film formed on a substrate placed inside an airtight processing chamber by inducing a processing gas into the processing chamber, in which the processing gas contains at least CF_4 and N_2 and the etching target film is constituted of an upper organic film containing Si and a lower SiO_2 film, is provided. It is to be noted that the processing gas may further contain Ar.